

2SD2573

Silicon NPN triple diffusion planar type

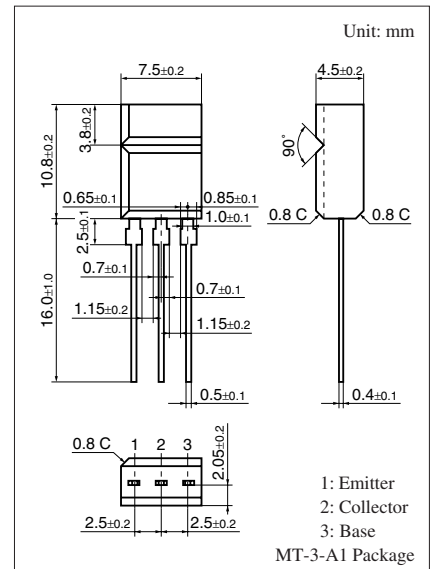
For high current amplification, power amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Allowing supply with the radial tapping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	80	V
Collector-emitter voltage (Base open)	V_{CEO}	60	V
Emitter-base voltage (Collector open)	V_{EBO}	6	V
Collector current	I_C	3	A
Peak collector current	I_{CP}	6	A
Collector power dissipation	$T_C = 25^\circ\text{C}$ P_C	1.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



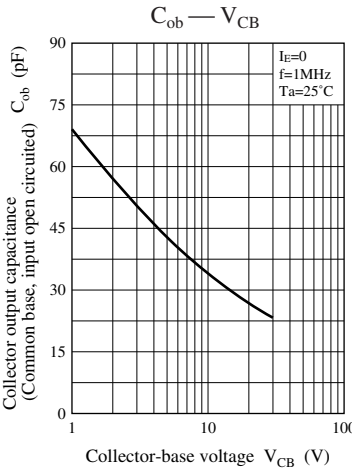
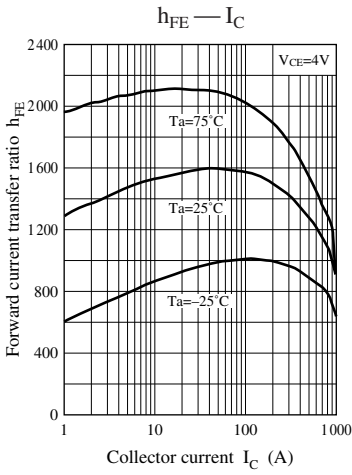
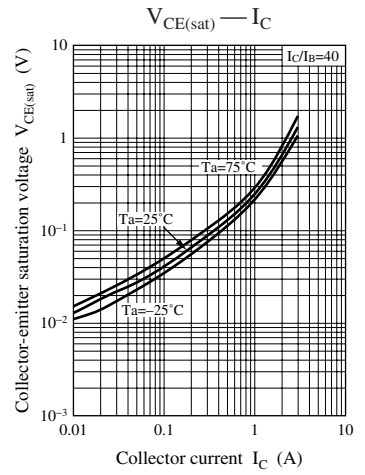
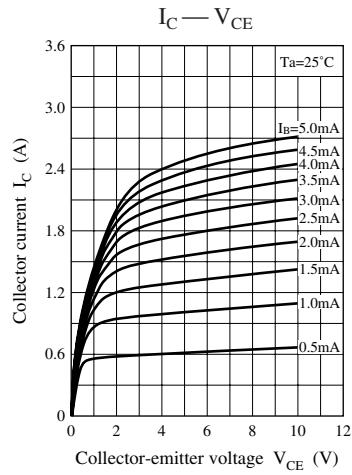
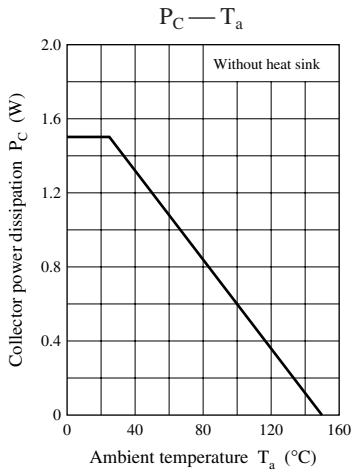
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 25\text{ mA}$, $I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 80\text{ V}$, $I_E = 0$			100	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CE} = 40\text{ V}$, $I_B = 0$			100	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6\text{ V}$, $I_C = 0$			100	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 4\text{ V}$, $I_C = 0.5\text{ A}$	500		2500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{ A}$, $I_B = 0.05\text{ A}$			1.0	V
Transition frequency	f_T	$V_{CE} = 12\text{ V}$, $I_C = 0.2\text{ A}$, $f = 10\text{ MHz}$		50		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	P	Q	R
h_{FE}	500 to 1000	800 to 1500	1200 to 2500



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